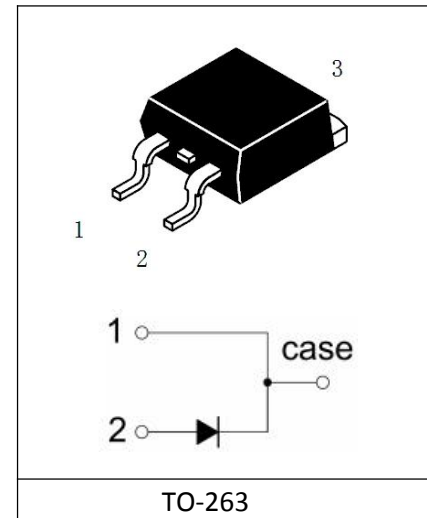


SCHOTTKY RECTIFIERS

Features:

- Low power loss,high efficiency
- High surge capacity
- High ESD capacity : HBM,3B (>8000V)
- For use in low voltage,high frequency inverters, free wheeling,and polarity protection applications
- Metal silicon junction,majority carrier conduction
- Guard ring for over voltage protection



Absolute Maximum Ratings($T_c=25^{\circ}\text{C}$):

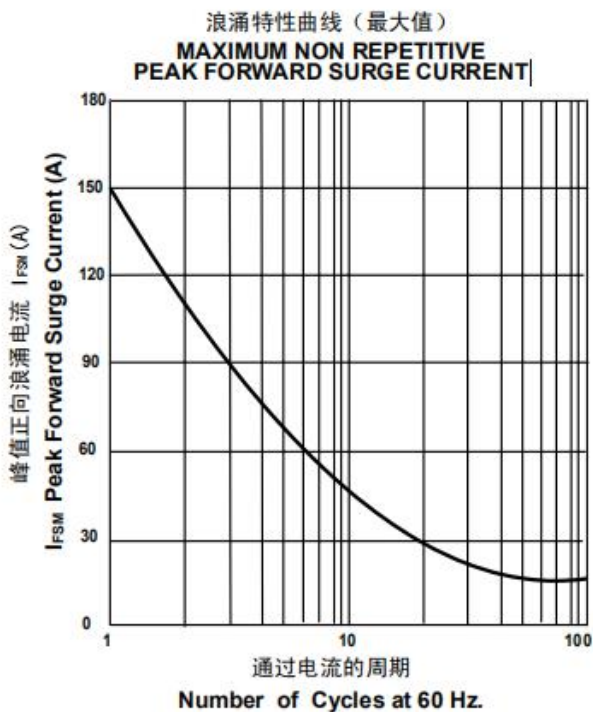
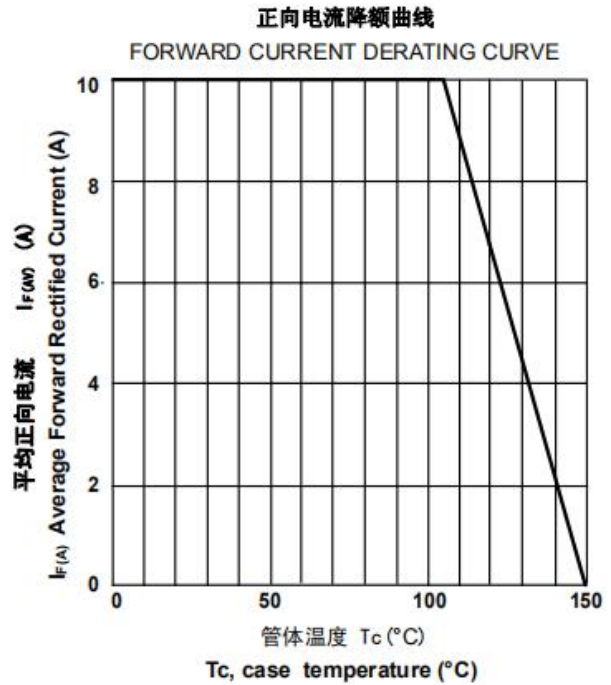
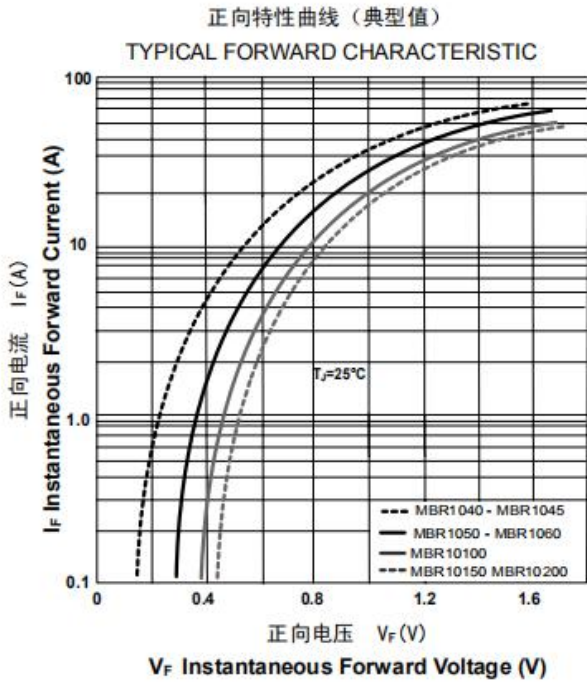
Characteristics	Symbol	Rating	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	40	V
Average Rectified Forward Current	$I_{F(AV)}$	10	A
Non-repetitive Peak Forward Surge Current 8.3ms Single Half-Sine-Wave	I_{FSM}	150	A
Collector power dissipation $T_a=25^{\circ}\text{C}$	P_{tot}	2.0	W
Junction temperature	T_j	125	$^{\circ}\text{C}$
Storage temperature range	T_{STG}	-55~150	$^{\circ}\text{C}$

Electrical Characteristics($T_c=25^{\circ}\text{C}$) :

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=10\text{A}; T_C=25^{\circ}\text{C}$			0.70	V
Reverse Current	I_R	$V_R=40\text{V}; T_C=25^{\circ}\text{C}$ $V_R=40\text{V}; T_C=100^{\circ}\text{C}$			0.10 15.0	mA
Peak Repetitive Reverse Surge Current	I_{RRM}	2.0 us Pulsu Width , $f=1.0\text{KHZ}$ $T_J<175^{\circ}\text{C}$			1.0	A

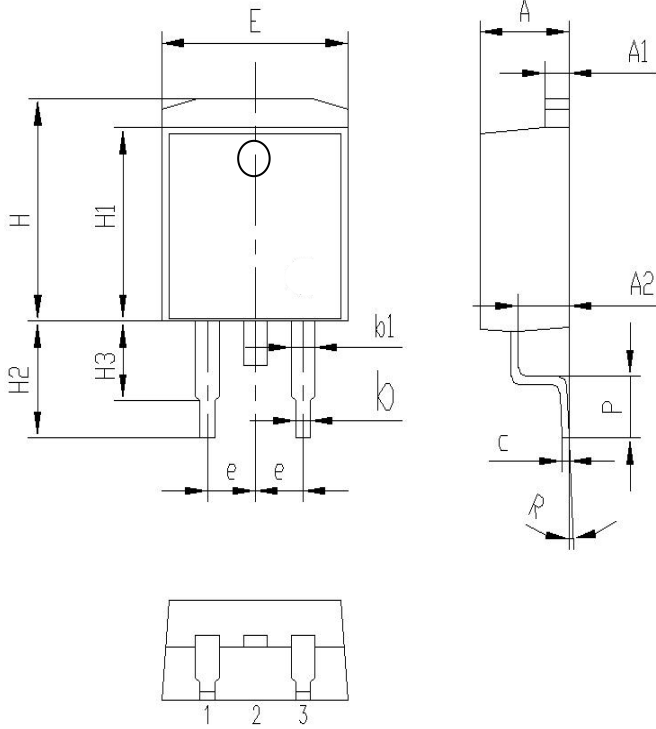
Symbol	Paramter	Typ	Units
$R_{\theta JA}$	Junction-to-Ambient	50	$^{\circ}\text{C}/\text{W}$

TYPICAL CHARACTERISTICS



Package Information

TO-263 PACKAGE



Symbol	Unit mm		
	Min	Typ	Max
A	4.40	4.6	4.80
A1	1.17	1.27	1.37
A2	2.40	2.6	2.80
b	0.60	0.8	1.00
b1	1.05	1.25	1.45
c	0.28	0.38	0.48
e	2.34	2.54	2.74
E	9.9	10.1	10.3
H	9.90	10.1	10.3
H1	8.50	8.7	8.90
H2	4.85	5.05	5.25
H3	3.60	3.8	4.00
R	0°	3°	6°
P	2.55	1.75	2.95